

Automotive-grade N-channel 100 V, 25 mΩ typ., 7.8 A STripFET™ F3 Power MOSFET in a PowerFLAT™ 5x6 package

Datasheet - production data

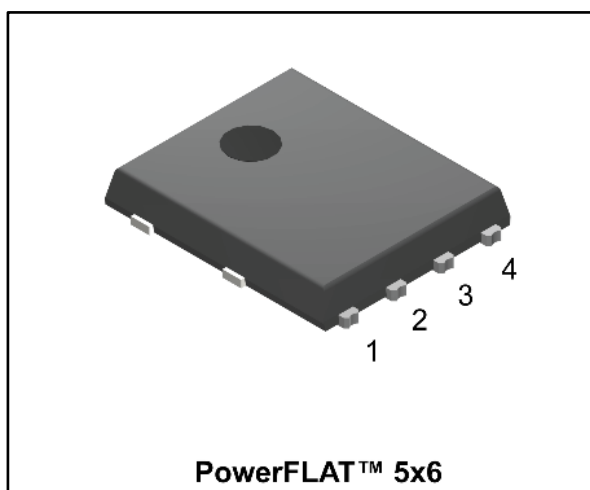
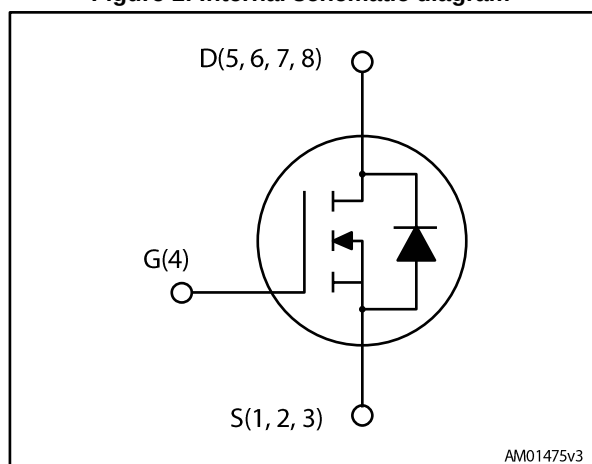


Figure 1: Internal schematic diagram



Features

Order code	V _{DS}	R _{DS(on)} max.	I _D
STL8N10LF3	100 V	35 mΩ	7.8 A



- AEC-Q101 qualified
- Logic level V_{GS(th)}
- 175 °C maximum junction temperature
- 100% avalanche rated
- Wettable flank package

Applications

- Switching applications

Description

This device is an N-channel Power MOSFET developed using STripFET™ F3 technology. It is designed to minimize on-resistance and gate charge to provide superior switching performance.

Table 1: Device summary

Order code	Marking	Package	Packing
STL8N10LF3	8N10LF3	PowerFLAT™ 5x6	Tape and reel

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1 Electrical ratings

Table 2: Absolute maximum ratings

Symbol	Parameter	Value	Unit
V_{DS}	Drain-source voltage	100	V
V_{GS}	Gate-source voltage	± 20	V
$I_D^{(1)}$	Drain current (continuous) at $T_C = 25\text{ }^\circ\text{C}$	20	A
$I_D^{(1)}$	Drain current (continuous) at $T_C = 100\text{ }^\circ\text{C}$	20	A
$I_D^{(2)}$	Drain current (continuous) at $T_{pcb} = 25\text{ }^\circ\text{C}$	7.8	A
$I_D^{(2)}$	Drain current (continuous) at $T_{pcb} = 100\text{ }^\circ\text{C}$	5.5	A
$I_{DM}^{(2)(3)}$	Drain current (pulsed)	31.2	A
$P_{TOT}^{(1)}$	Total dissipation at $T_C = 25\text{ }^\circ\text{C}$	70	W
$P_{TOT}^{(2)}$	Total dissipation at $T_{pcb} = 25\text{ }^\circ\text{C}$	4.3	W
I_{AV}	Not-repetitive avalanche current	7.8	A
$E_{AS}^{(4)}$	Single pulse avalanche energy	190	mJ
T_J	Operating junction temperature range	-55 to 175	$^\circ\text{C}$
T_{stg}	Storage temperature range		

Notes:

- (1) This value is rated according to $R_{thj-case}$ and limited by package
 (2) This value is rated according to $R_{thj-pcb}$
 (3) Pulse width limited by safe operating area.
 (4) Starting $T_J = 25\text{ }^\circ\text{C}$, $I_D = 7.8\text{ A}$, $V_{DD} = 25\text{ V}$.

Table 3: Thermal resistance

Symbol	Parameter	Value	Unit
$R_{thj-case}$	Thermal resistance junction-case	2.1	$^\circ\text{C/W}$
$R_{thj-pcb}^{(1)}$	Thermal resistance junction-pcb	35	$^\circ\text{C/W}$

Notes:

- (1) When mounted on FR-4 board of 1 inch², 2oz Cu, $t < 10\text{ s}$

2 Electrical characteristics

(T_C = 25 °C unless otherwise specified)

Table 4: On/Off states

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
V _{(BR)DSS}	Drain-source breakdown voltage	V _{GS} = 0 V, I _D = 250 μA	100			V
I _{DSS}	Zero gate voltage drain current	V _{GS} = 0 V, V _{DS} = 100 V			1	μA
I _{GSS}	Gate-body leakage current	V _{DS} = 0 V, V _{GS} = ±20 V			±100	nA
V _{GS(th)}	Gate threshold voltage	V _{DS} = V _{GS} , I _D = 250 μA	1		3	V
R _{DS(on)}	Static drain-source on-resistance	V _{GS} = 10 V, I _D = 4 A		25	35	mΩ
		V _{GS} = 5 V, I _D = 4 A		40	50	mΩ

Table 5: Dynamic

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
C _{iss}	Input capacitance	V _{DS} = 25 V, f = 1 MHz, V _{GS} = 0 V	-	970	-	pF
C _{oss}	Output capacitance		-	115	-	
C _{rss}	Reverse transfer capacitance		-	11.5	-	
Q _g	Total gate charge	V _{DD} = 50 V, I _D = 7.8 A, V _{GS} = 10 V (see Figure 13: "Test circuit for gate charge behavior")	-	20.5	-	nC
Q _{gs}	Gate-source charge		-	4	-	
Q _{gd}	Gate-drain charge		-	5	-	
R _G	Intrinsic gate resistance	f = 1 MHz open drain	-	3.65	-	Ω

Table 6: Switching times

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
t _{d(on)}	Turn-on delay time	V _{DD} = 50 V, I _D = 7.8 A, R _G = 4.7 Ω, V _{GS} = 10 V (see Figure 12: "Test circuit for resistive load switching times")	-	8.7	-	ns
t _r	Rise time		-	9.6	-	
t _{d(off)}	Turn-off delay time		-	50.6	-	
t _f	Fall time		-	5.2	-	

Table 7: Source-drain diode

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
I_{SD}	Source-drain current		-		7.8	A
$I_{SDM}^{(1)}$	Source-drain current (pulsed)		-		31.2	A
$V_{SD}^{(2)}$	Forward on voltage	$I_{DS} = 7.8 \text{ A}$, $V_{GS} = 0$			1.3	V
t_{rr}	Reverse recovery time	$I_{SD} = 7.8 \text{ A}$, $di/dt = 100 \text{ A}/\mu\text{s}$ $V_{DD} = 48 \text{ V}$, $T_j = 150 \text{ }^\circ\text{C}$ (see <i>Figure 14: "Test circuit for inductive load switching and diode recovery times")</i>)	-	42.5		ns
Q_{rr}	Reverse recovery charge		-	87		nC
I_{RRM}	Reverse recovery current		-	4.08		A

Notes:

⁽¹⁾Pulse width limited by safe operating area

⁽²⁾Pulsed: pulse duration = 300 μs , duty cycle 1.5 %

2.1 Electrical characteristics (curves)

Figure 2: Safe operating area

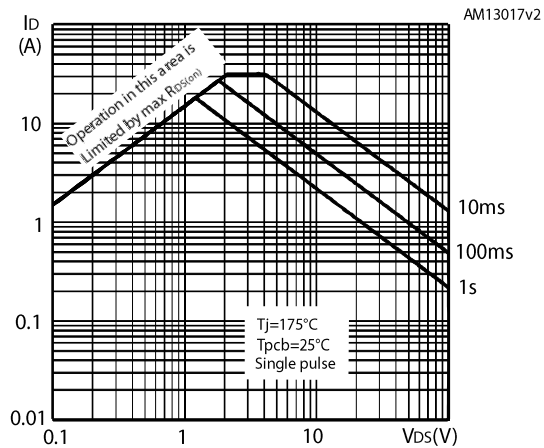


Figure 3: Thermal impedance

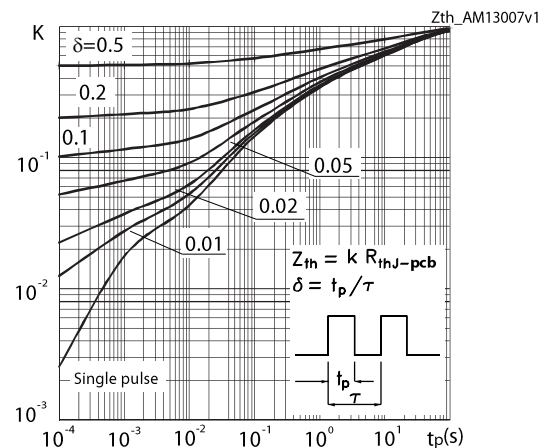


Figure 4: Output characteristics

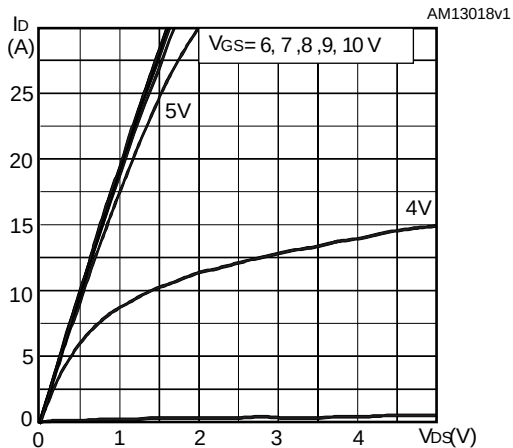


Figure 5: Transfer characteristics

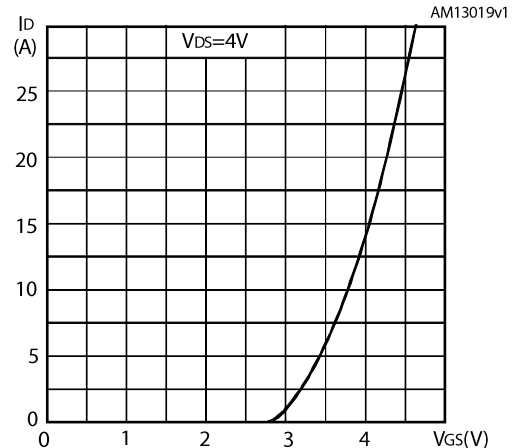


Figure 6: Normalized V(BR)DSS vs temperature

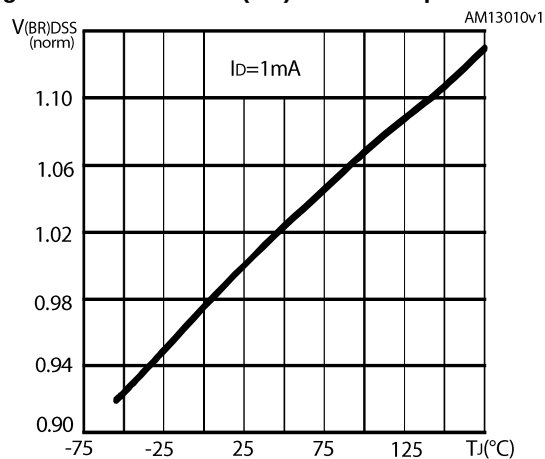


Figure 7: Static drain-source on-resistance

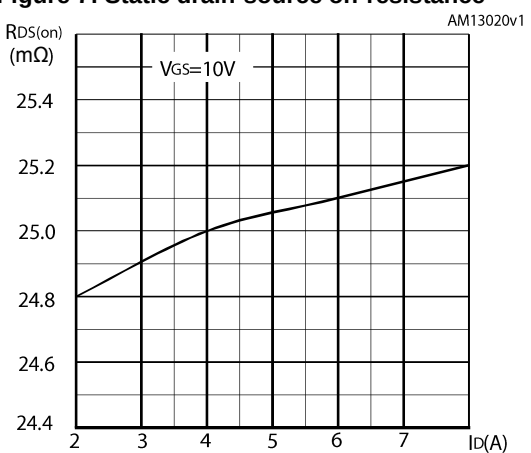


Figure 8: Gate charge vs gate-source voltage

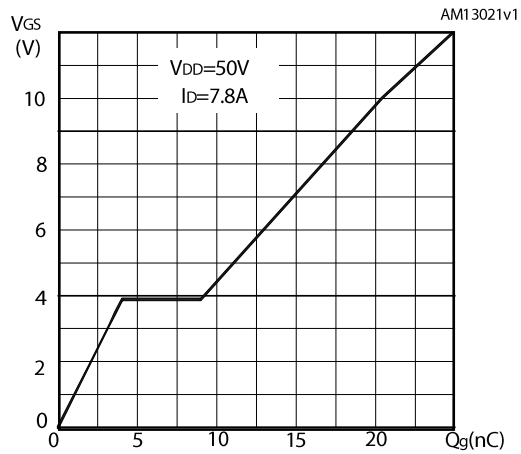


Figure 9: capacitance variation

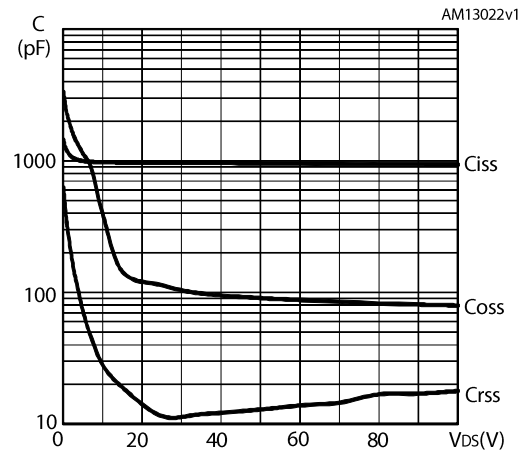


Figure 10: Normalized gate threshold voltage vs temperature

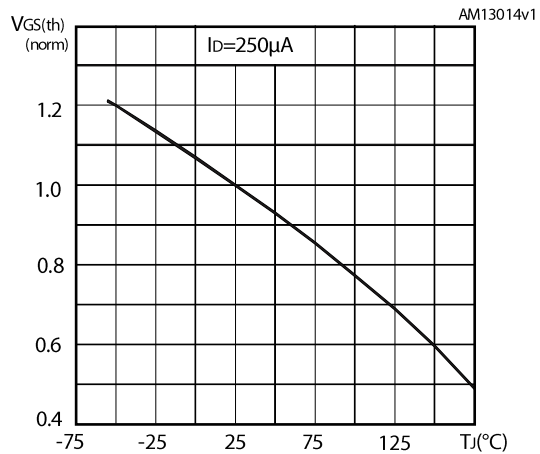
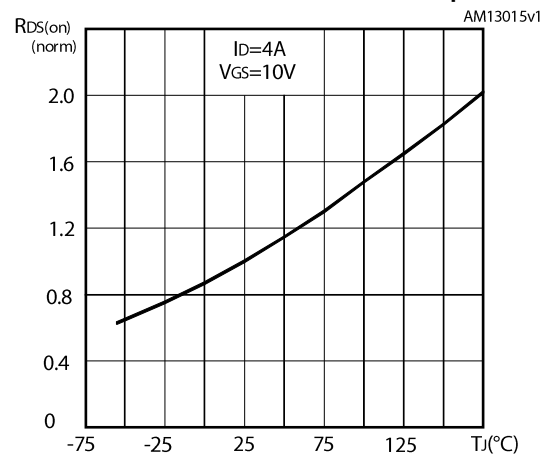


Figure 11: Normalized on resistance vs temperature



AM01468v1

AM01469v1

AM01470v1

AM01471v1

AM01472v1

AM01473v1

4 Package information

In order to meet environmental requirements, ST offers these devices in different grades of ECOPACK® packages, depending on their level of environmental compliance. ECOPACK® specifications, grade definitions and product status are available at: www.st.com. ECOPACK® is an ST trademark.

4.1 PowerFLAT 5x6 type R package information

Figure 18: PowerFLAT™ 5x6 WF type R package outline

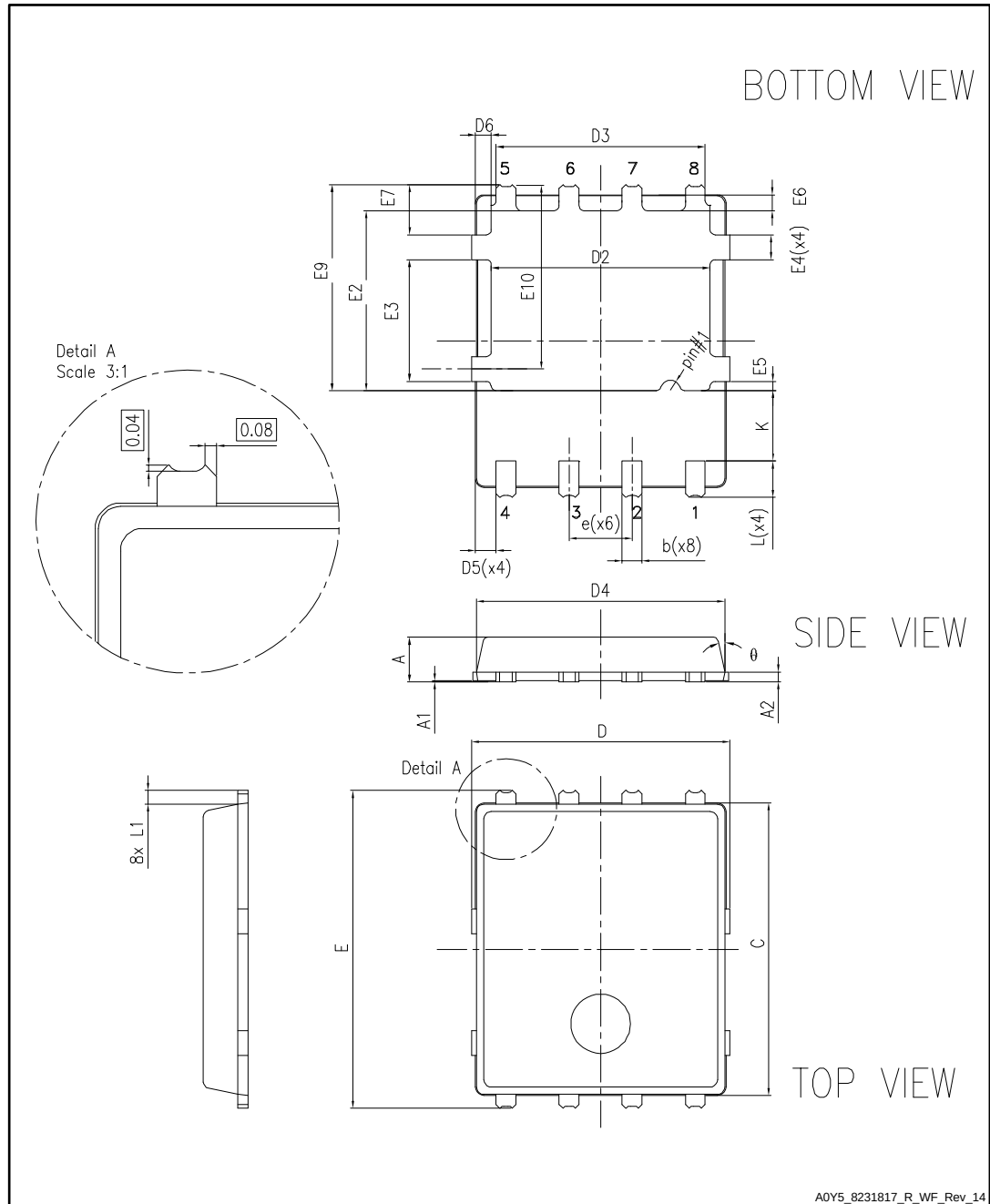
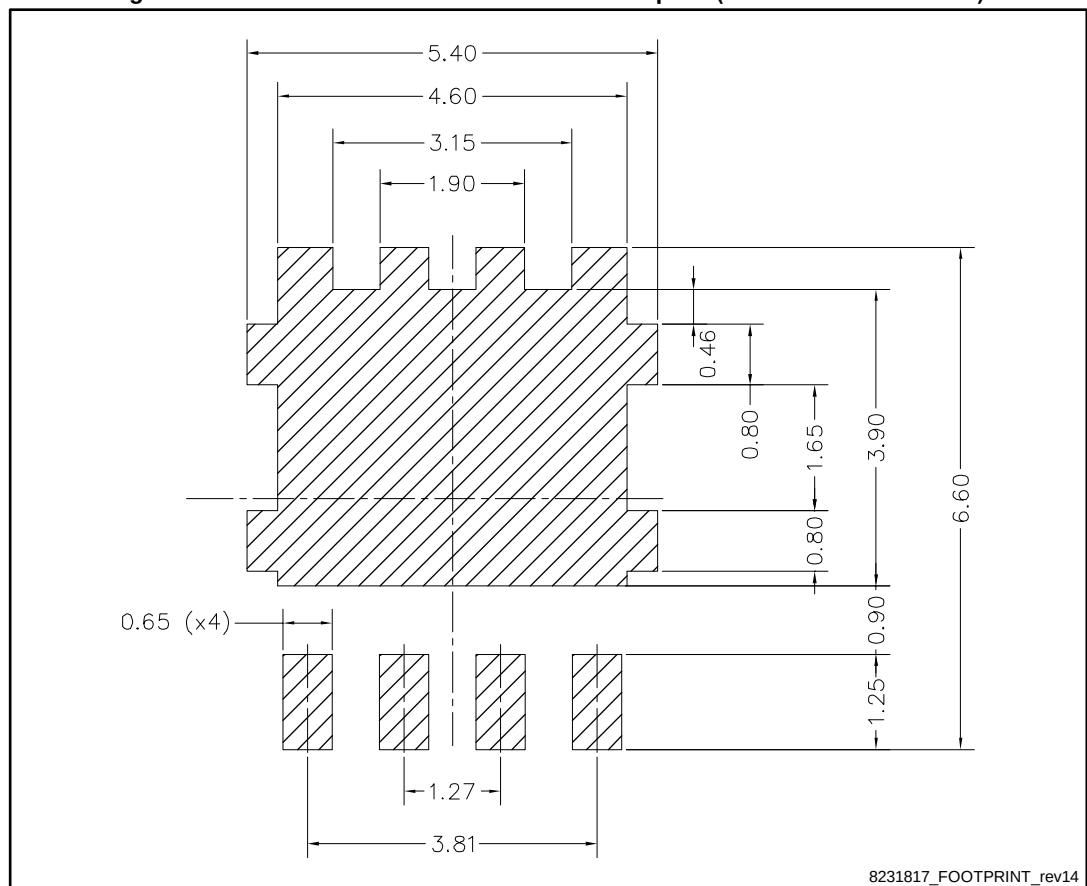


Table 8: PowerFLAT™ 5x6 WF type R mechanical data

Dim.	mm		
	Min.	Typ.	Max.
A	0.80		1.00
A1	0.02		0.05
A2		0.25	
b	0.30		0.50
C	5.80	6.00	6.10
D	5.00	5.20	5.40
D2	4.15		4.45
D3	4.05	4.20	4.35
D4	4.80	5.00	5.10
D5	0.25	0.4	0.55
D6	0.15	0.3	0.45
e		1.27	
E	6.20	6.40	6.60
E2	3.50		3.70
E3	2.35		2.55
E4	0.40		0.60
E5	0.08		0.28
E6	0.20	0.325	0.45
E7	0.85	1.00	1.15
E9	4.00	4.20	4.40
E10	3.55	3.70	3.85
K	1.275		1.575
L	0.725	0.825	0.925
L1	0.175	0.275	0.375
Θ	0°		12°

Figure 19: PowerFLAT™ 5x6 recommended footprint (dimensions are in mm)



4.2 Packing information

Figure 20: PowerFLAT™ 5x6 WF tape (dimensions are in mm)

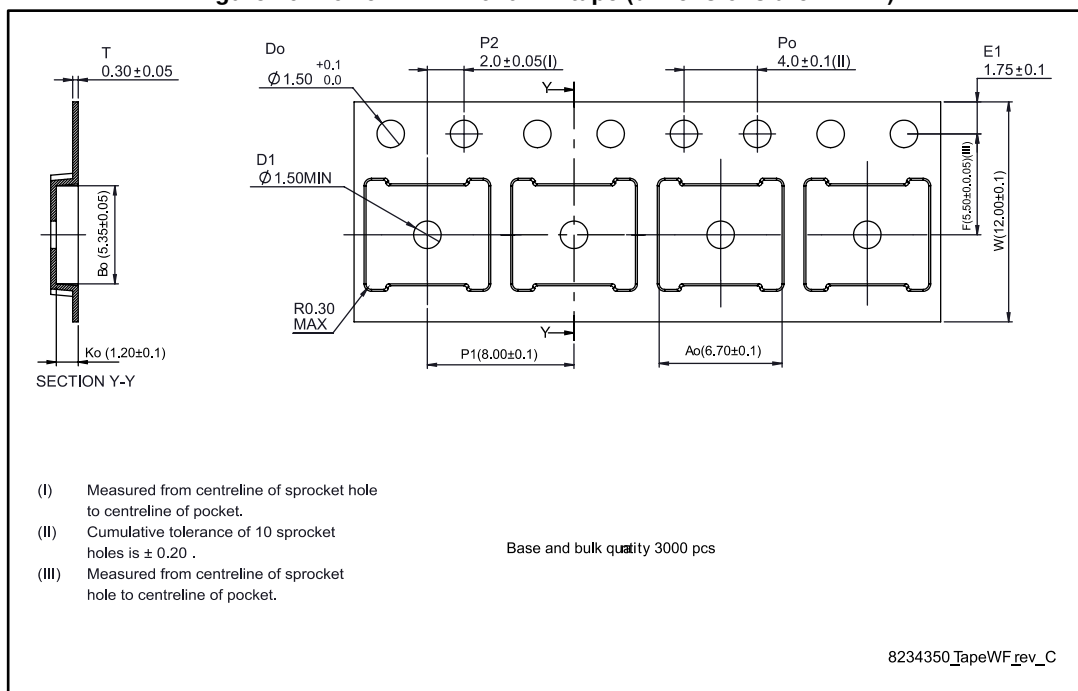


Figure 21: PowerFLAT™ 5x6 package orientation in carrier tape

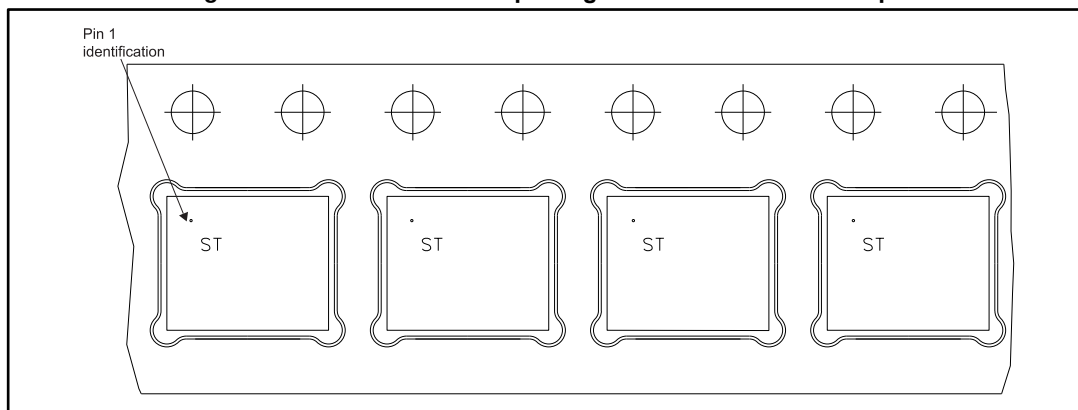
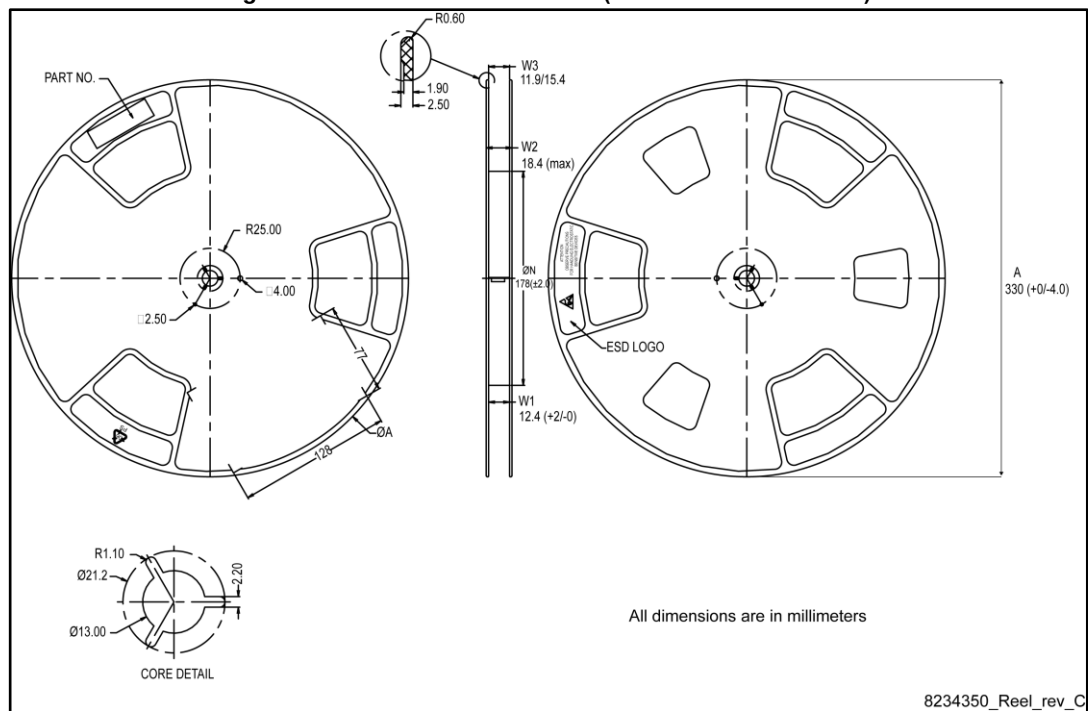


Figure 22: PowerFLAT™ 5x6 reel (dimensions are in mm)



5 Revision history

Table 9: Document revision history

Date	Revision	Changes
17-Jan-2013	1	First release.
18-May-2015	2	Updated Section 4: Package information. Added Section 5: Packing information. Minor text changes.
09-Nov-2016	3	Updated features in cover page and <i>Table 2: Absolute maximum ratings</i> . Updated <i>Section 4: Package information</i> Minor text changes
28-Nov-2016	4	Updated test conditions in <i>Table 4: "On/Off states"</i> .

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